



BUK9K22-80E

Dual N-channel 80 V, 22 mΩ logic level MOSFET

11 May 2018

Product data sheet

1. General description

Dual Logic level N-channel MOSFET in an LPAK56D (Dual Power-SO8) package using TrenchMOS technology. This product has been designed and qualified to AEC-Q101 standard for use in high performance automotive applications.

2. Features and benefits

- Dual MOSFET
- AEC-Q101 compliant
- Repetitive avalanche rated
- Suitable for thermally demanding environments due to 175 °C rating
- True logic level gate with $V_{GS(th)}$ rating of greater than 0.5 V at 175 °C

3. Applications

- 12 V, 24 V and 48 V automotive systems
- Motors, lamps and solenoid control
- Transmission control
- Ultra high performance power switching

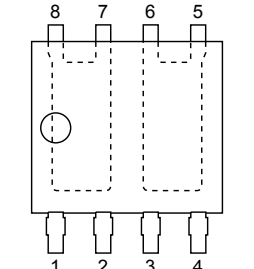
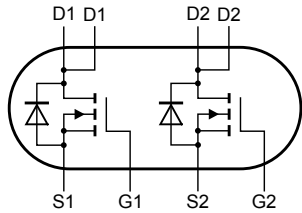
4. Quick reference data

Table 1. Quick reference data

Symbol	Parameter	Conditions	Min	Typ	Max	Unit
Limiting values FET1 and FET2						
V_{DS}	drain-source voltage	$25\text{ °C} \leq T_j \leq 175\text{ °C}$	-	-	80	V
I_D	drain current	$V_{GS} = 5\text{ V}$; $T_{mb} = 25\text{ °C}$; Fig. 2	-	-	21	A
P_{tot}	total power dissipation	$T_{mb} = 25\text{ °C}$; Fig. 1	-	-	64	W
T_j	junction temperature		-55	-	175	°C
Static characteristics FET1 and FET2						
R_{DSon}	drain-source on-state resistance	$V_{GS} = 5\text{ V}$; $I_D = 10\text{ A}$; $T_j = 175\text{ °C}$; Fig. 12	-	-	54.5	mΩ
		$V_{GS} = 5\text{ V}$; $I_D = 10\text{ A}$; $T_j = 25\text{ °C}$; Fig. 11	-	15.7	21.7	mΩ
Dynamic characteristics FET1 and FET2						
Q_{GD}	gate-drain charge	$I_D = 10\text{ A}$; $V_{DS} = 64\text{ V}$; $V_{GS} = 5\text{ V}$; $T_j = 25\text{ °C}$; Fig. 13 ; Fig. 14	-	8.4	-	nC
$Q_{G(tot)}$	total gate charge		-	23.1	-	nC

5. Pinning information

Table 2. Pinning information

Pin	Symbol	Description	Simplified outline	Graphic symbol
1	S1	source1	 <p>LFPAK56D (SOT1205)</p>	 <p>mbk725</p>
2	G1	gate1		
3	S2	source2		
4	G2	gate2		
5	D2	drain2		
6	D2	drain2		
7	D1	drain1		
8	D1	drain1		

6. Ordering information

Table 3. Ordering information

Type number	Package		Version
	Name	Description	
BUK9K22-80E	LFPAK56D	plastic, single ended surface mounted package (LFPAK56D); 8 leads	SOT1205

7. Marking

Table 4. Marking codes

Type number	Marking code
BUK9K22-80E	92280E

8. Limiting values

Table 5. Limiting values

In accordance with the Absolute Maximum Rating System (IEC 60134).

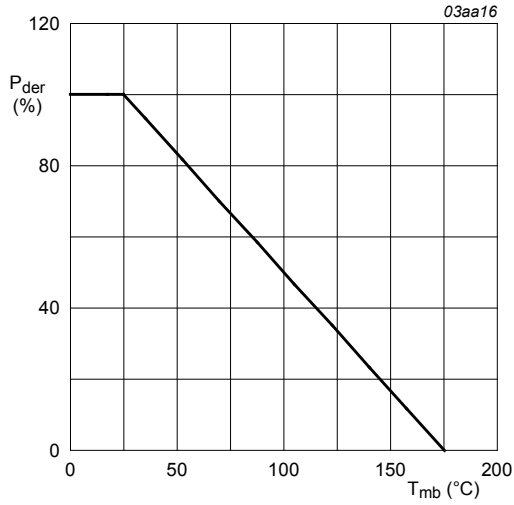
Symbol	Parameter	Conditions	Min	Max	Unit
Limiting values FET1 and FET2					
V_{DS}	drain-source voltage	$25\text{ °C} \leq T_j \leq 175\text{ °C}$	-	80	V
V_{DGR}	drain-gate voltage	$R_{GS} = 20\text{ k}\Omega$	-	80	V
V_{GS}	gate-source voltage	DC; $T_j \leq 175\text{ °C}$	-10	10	V
		Pulsed; $T_j \leq 175\text{ °C}$	[1] [2]	15	V
P_{tot}	total power dissipation	$T_{mb} = 25\text{ °C}$; Fig. 1	-	64	W
I_D	drain current	$V_{GS} = 5\text{ V}$; $T_{mb} = 25\text{ °C}$; Fig. 2	-	21	A
		$V_{GS} = 5\text{ V}$; $T_{sp} = 100\text{ °C}$; Fig. 2	-	15	A
I_{DM}	peak drain current	pulsed; $t_p \leq 10\text{ }\mu\text{s}$; $T_{mb} = 25\text{ °C}$; Fig. 3	-	84	A
T_{stg}	storage temperature		-55	175	°C
T_j	junction temperature		-55	175	°C
Source-drain diode FET1 and FET2					
I_S	source current	$T_{mb} = 25\text{ °C}$	-	21	A
I_{SM}	peak source current	pulsed; $t_p \leq 10\text{ }\mu\text{s}$; $T_{mb} = 25\text{ °C}$	-	84	A
Avalanche ruggedness FET1 and FET2					
$E_{DS(AL)S}$	non-repetitive drain-source avalanche energy	$I_D = 21\text{ A}$; $V_{sup} \leq 80\text{ V}$; $R_{GS} = 50\text{ }\Omega$; $V_{GS} = 5\text{ V}$; $T_{j(init)} = 25\text{ °C}$; unclamped; Fig. 4	[3] [4]	116	mJ

[1] Accumulated pulse duration up to 50 hours delivers zero defect ppm

[2] Significantly longer life times are achieved by lowering T_j and/or V_{GS}

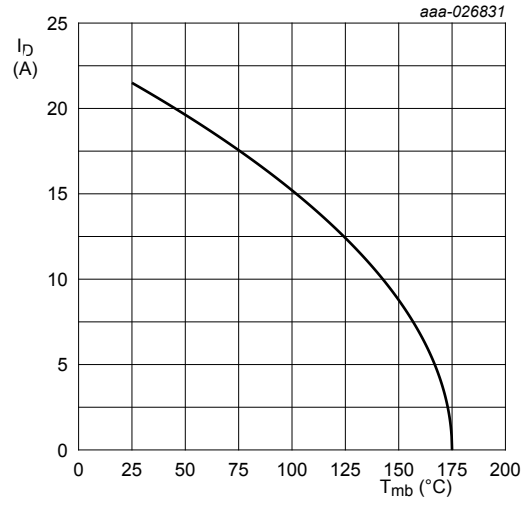
[3] Single-pulse avalanche rating limited by maximum junction temperature of 175 °C

[4] Refer to application note AN10273 for further information



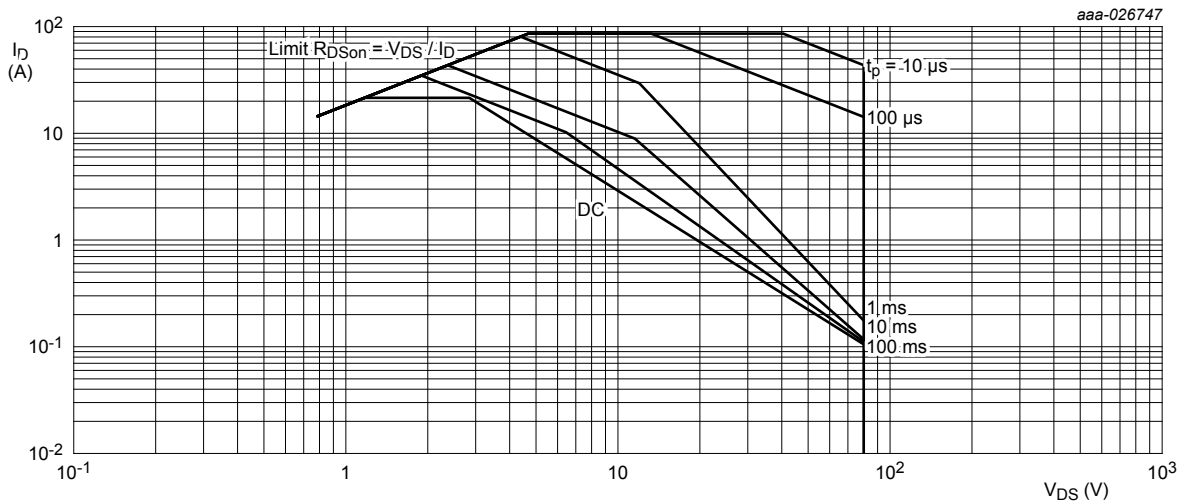
$$P_{der} = \frac{P_{tot}}{P_{tot(25^\circ C)}} \times 100\%$$

Fig. 1. Normalized total power dissipation as a function of mounting base temperature



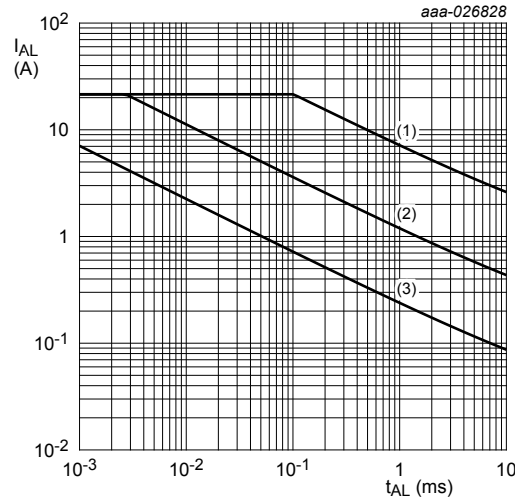
$V_{GS} \geq 5\text{ V}$

Fig. 2. Continuous drain current as a function of mounting base temperature, FET1 and FET2



$T_{mb} = 25\text{ }^\circ\text{C}$; I_{DM} is a single pulse

Fig. 3. Safe operating area; continuous and peak drain currents as a function of drain-source voltage, FET1 and FET2



(1) $T_{j\text{ (init)}} = 25^{\circ}\text{C}$; (2) $T_{j\text{ (init)}} = 150^{\circ}\text{C}$; (3) Repetitive Avalanche

Fig. 4. Avalanche rating; avalanche current as a function of avalanche time, FET1 and FET2

9. Thermal characteristics

Table 6. Thermal characteristics

Symbol	Parameter	Conditions	Min	Typ	Max	Unit
$R_{th(j-mb)}$	thermal resistance from junction to mounting base	Fig. 5	-	-	2.36	K/W
$R_{th(j-a)}$	thermal resistance from junction to ambient	Minimum footprint; mounted on a printed circuit board	-	95	-	K/W

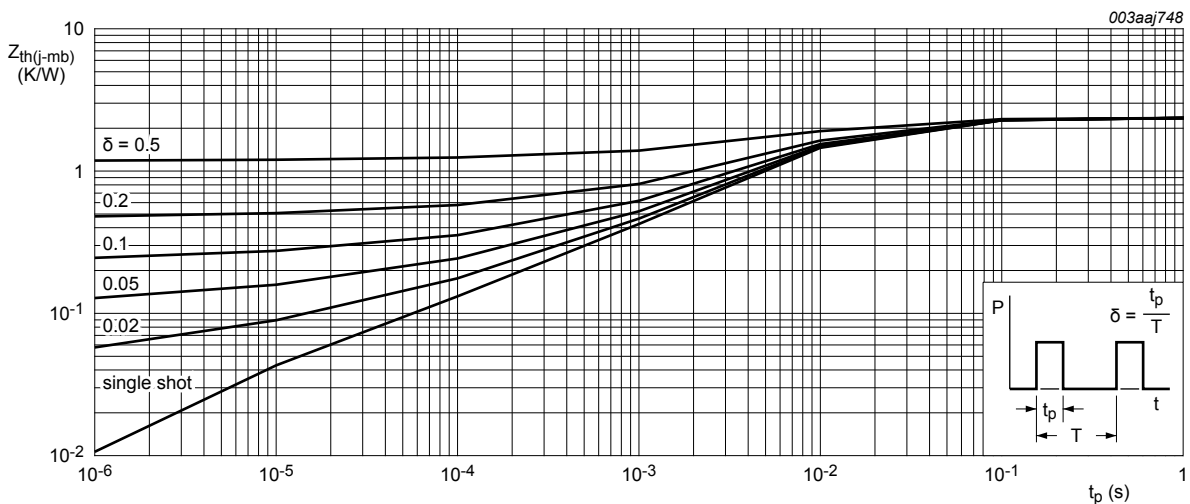


Fig. 5. Transient thermal impedance from junction to mounting base as a function of pulse duration, FET1 and FET2

10. Characteristics

Table 7. Characteristics

Symbol	Parameter	Conditions	Min	Typ	Max	Unit
Static characteristics FET1 and FET2						
$V_{(BR)DSS}$	drain-source breakdown voltage	$I_D = 250 \mu A; V_{GS} = 0 V; T_j = 25 \text{ }^\circ C$	80	-	-	V
		$I_D = 250 \mu A; V_{GS} = 0 V; T_j = -55 \text{ }^\circ C$	72	-	-	V
$V_{GS(th)}$	gate-source threshold voltage	$I_D = 1 \text{ mA}; V_{DS}=V_{GS}; T_j = 25 \text{ }^\circ C$; Fig. 9 ; Fig. 10	1.4	1.7	2.1	V
		$I_D = 1 \text{ mA}; V_{DS}=V_{GS}; T_j = -55 \text{ }^\circ C$; Fig. 10	-	-	2.45	V
		$I_D = 1 \text{ mA}; V_{DS}=V_{GS}; T_j = 175 \text{ }^\circ C$; Fig. 10	0.5	-	-	V
I_{DSS}	drain leakage current	$V_{DS} = 80 V; V_{GS} = 0 V; T_j = 25 \text{ }^\circ C$	-	0.01	1	μA
		$V_{DS} = 80 V; V_{GS} = 0 V; T_j = 175 \text{ }^\circ C$	-	-	500	μA
I_{GSS}	gate leakage current	$V_{GS} = 10 V; V_{DS} = 0 V; T_j = 25 \text{ }^\circ C$	-	2	100	nA
		$V_{GS} = -10 V; V_{DS} = 0 V; T_j = 25 \text{ }^\circ C$	-	2	100	nA
$R_{DS(on)}$	drain-source on-state resistance	$V_{GS} = 5 V; I_D = 10 A; T_j = 25 \text{ }^\circ C$; Fig. 11	-	15.7	21.7	mΩ
		$V_{GS} = 10 V; I_D = 10 A; T_j = 25 \text{ }^\circ C$; Fig. 11	-	14.4	19	mΩ
		$V_{GS} = 5 V; I_D = 10 A; T_j = 175 \text{ }^\circ C$; Fig. 12	-	-	54.5	mΩ
Dynamic characteristics FET1 and FET2						
$Q_{G(tot)}$	total gate charge	$I_D = 10 A; V_{DS} = 64 V; V_{GS} = 5 V; T_j = 25 \text{ }^\circ C$; Fig. 13 ; Fig. 14	-	23.1	-	nC
Q_{GS}	gate-source charge		-	5.4	-	nC
Q_{GD}	gate-drain charge		-	8.4	-	nC
C_{iss}	input capacitance	$V_{DS} = 25 V; V_{GS} = 0 V; f = 1 \text{ MHz}; T_j = 25 \text{ }^\circ C$; Fig. 15	-	2342	3115	pF
C_{oss}	output capacitance		-	170	204	pF
C_{rSS}	reverse transfer capacitance		-	89	122	pF
$t_{d(on)}$	turn-on delay time	$V_{DS} = 60 V; R_L = 5 \Omega; V_{GS} = 5 V; R_{G(ext)} = 5 \Omega; T_j = 25 \text{ }^\circ C$	-	13.9	-	ns
t_r	rise time		-	24.9	-	ns
$t_{d(off)}$	turn-off delay time		-	28.6	-	ns
t_f	fall time		-	20.6	-	ns
Source-drain diode FET1 and FET2						
V_{SD}	source-drain voltage	$I_S = 10 A; V_{GS} = 0 V; T_j = 25 \text{ }^\circ C$; Fig. 16	-	0.8	1.2	V
t_{rr}	reverse recovery time	$I_S = 10 A; di_S/dt = -100 A/\mu s; V_{GS} = 0 V; V_{DS} = 25 V; T_j = 25 \text{ }^\circ C$	-	28.4	-	ns
Q_r	recovered charge		-	33	-	nC

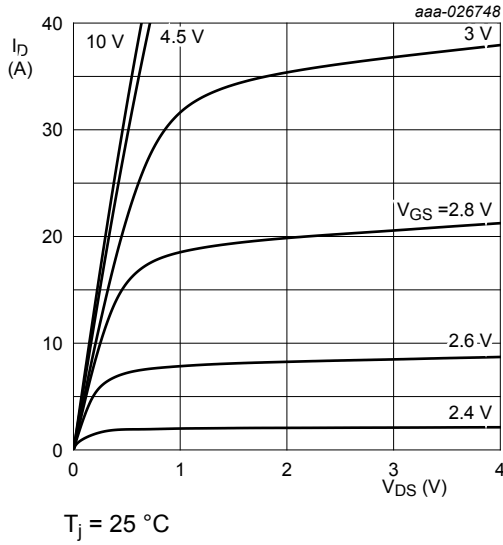


Fig. 6. Output characteristics; drain current as a function of drain-source voltage; typical values, FET1 and FET2

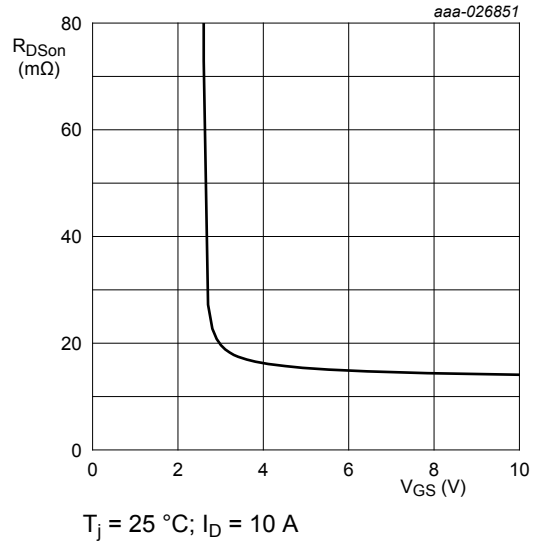


Fig. 7. Drain-source on-state resistance as a function of gate-source voltage; typical values, FET1 and FET2

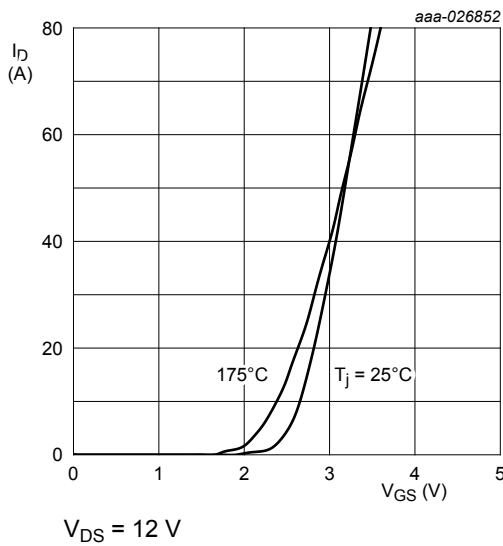


Fig. 8. Transfer characteristics; drain current as a function of gate-source voltage; typical values, FET1 and FET2

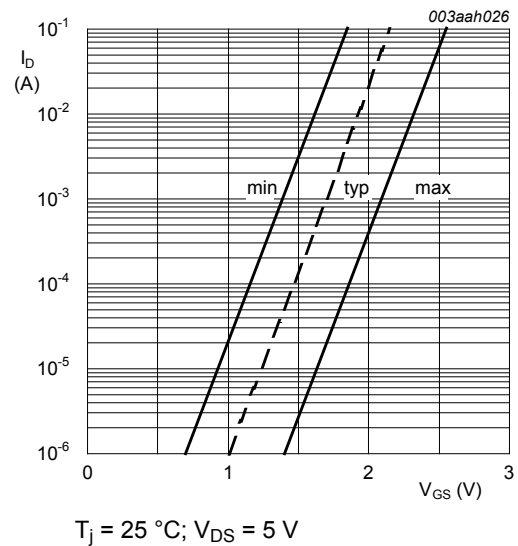
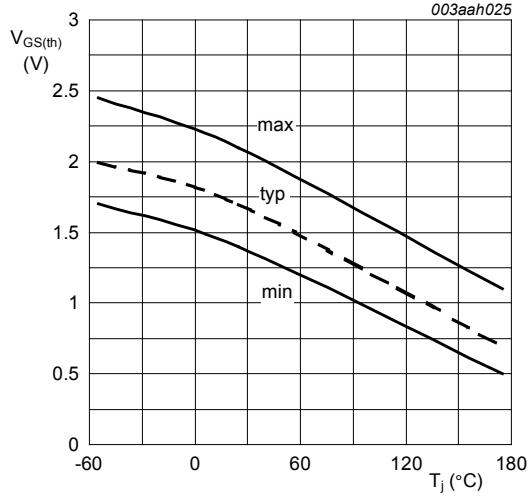
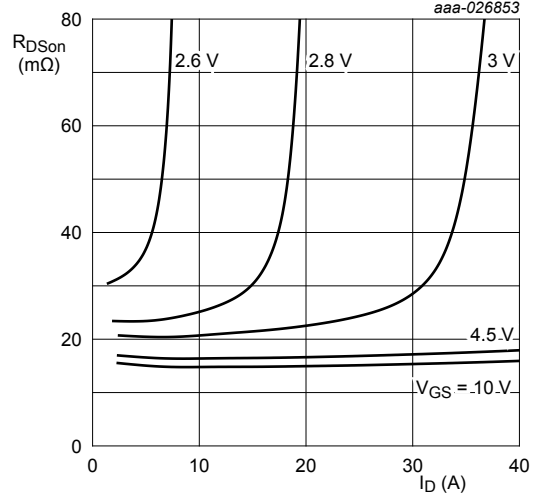


Fig. 9. Sub-threshold drain current as a function of gate-source voltage, FET1 and FET2



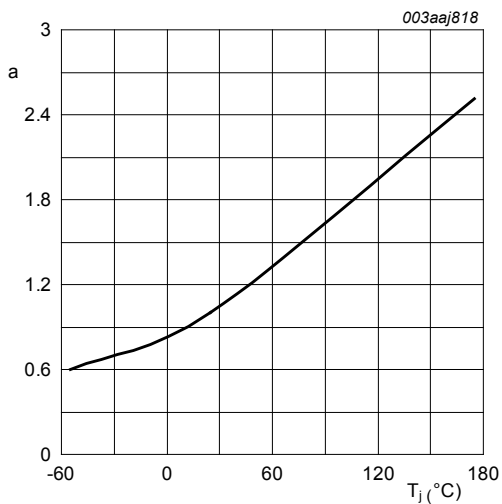
$I_D = 1 \text{ mA} ; V_{DS} = V_{GS}$

Fig. 10. Gate-source threshold voltage as a function of junction temperature, FET1 and FET2



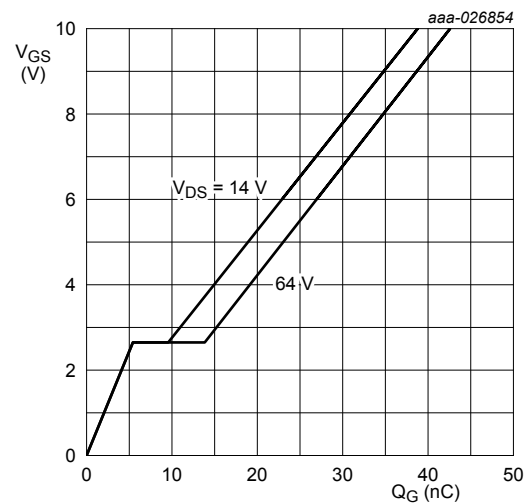
$T_j = 25 \text{ °C}$

Fig. 11. Drain-source on-state resistance as a function of drain current; typical values, FET1 and FET2



$$a = \frac{R_{DSon}}{R_{DSon}(25^\circ\text{C})}$$

Fig. 12. Normalized drain-source on-state resistance factor as a function of junction temperature, FET1 and FET2



$T_j = 25 \text{ °C} ; I_D = 10 \text{ A}$

Fig. 13. Gate-source voltage as a function of gate charge; typical values, FET1 and FET2

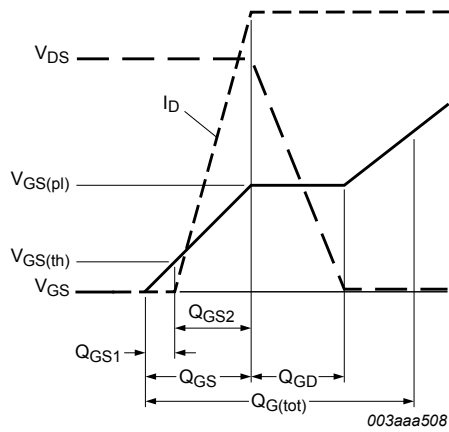
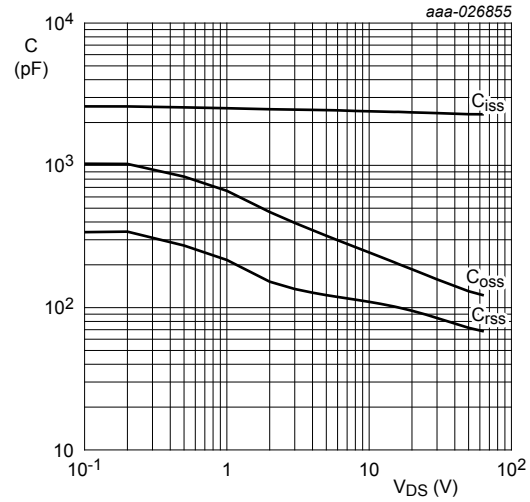
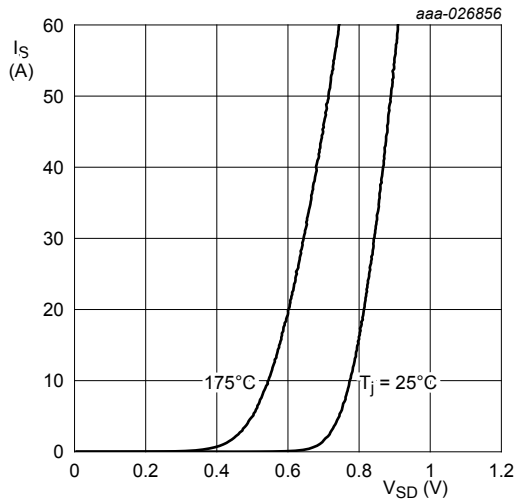


Fig. 14. Gate charge waveform definitions



$V_{GS} = 0 \text{ V}; f = 1 \text{ MHz}$

Fig. 15. Input, output and reverse transfer capacitances as a function of drain-source voltage; typical values, FET1 and FET2



$V_{GS} = 0 \text{ V}$

Fig. 16. Source-drain (diode forward) current as a function of source-drain (diode forward) voltage; typical values, FET1 and FET2

11. Package outline

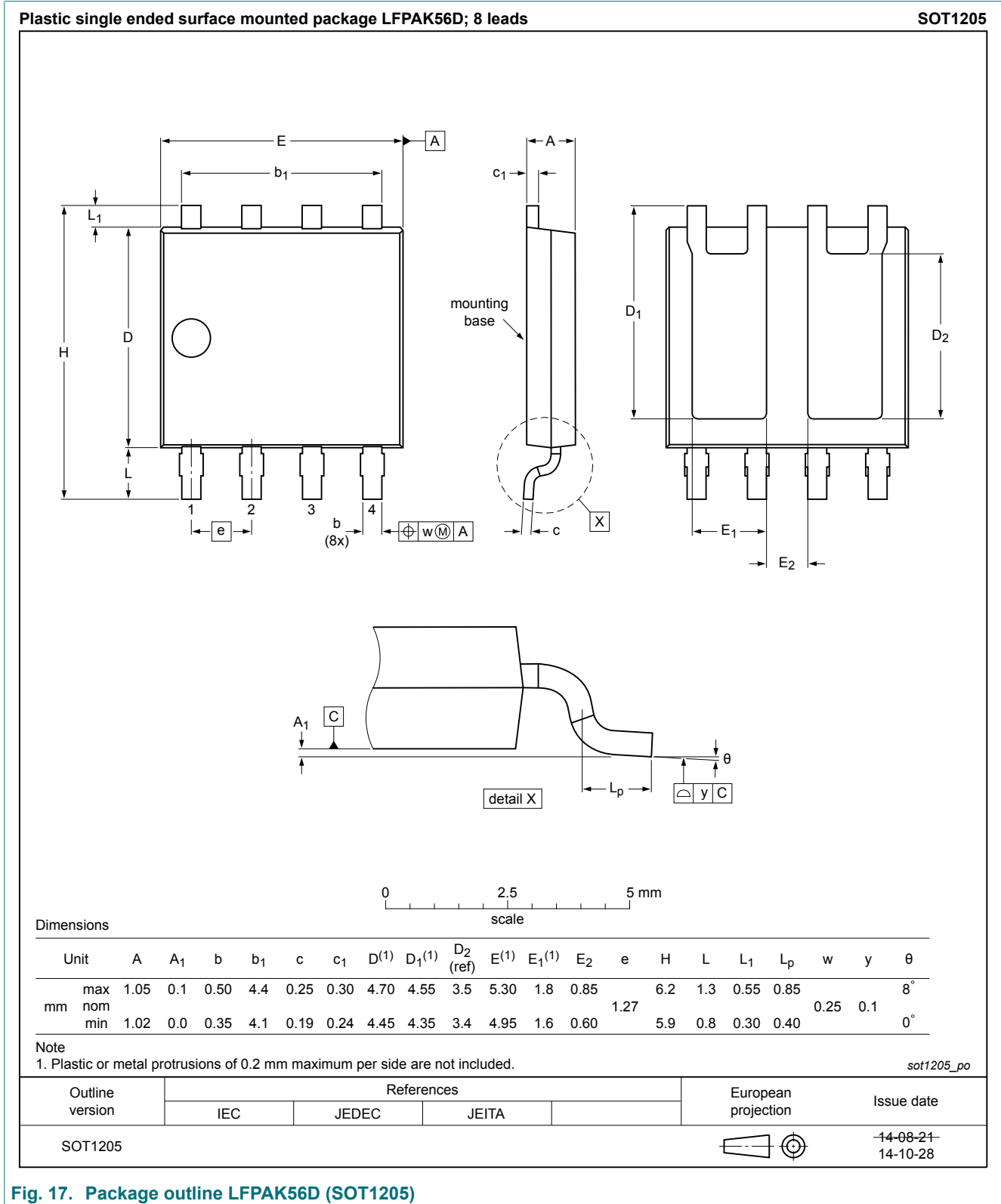


Fig. 17. Package outline LFAK56D (SOT1205)

12. Legal information

Data sheet status

Document status [1][2]	Product status [3]	Definition
Objective [short] data sheet	Development	This document contains data from the objective specification for product development.
Preliminary [short] data sheet	Qualification	This document contains data from the preliminary specification.
Product [short] data sheet	Production	This document contains the product specification.

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